Retriggerable Monostable Multivibrators

These dc triggered multivibrators feature pulse width control by three methods. The basic pulse width is programmed by selection of external resistance and capacitance values. The LS122 has an internal timing resistor that allows the circuits to be used with only an external capacitor. Once triggered, the basic pulse width may be extended by retriggering the gated low-level-active (A) or high-level-active (B) inputs, or be reduced by use of the overriding clear.

- Overriding Clear Terminates Output Pulse
- Compensated for V_{CC} and Temperature Variations
- DC Triggered from Active-High or Active-Low Gated Logic Inputs
- Retriggerable for Very Long Output Pulses, up to 100% Duty Cycle
- Internal Timing Resistors on LS122

GUARANTEED OPERATING RANGES

Symbol	Parameter	Min	Тур	Max	Unit
VCC	Supply Voltage	4.75	5.0	5.25	V
T _A	Operating Ambient Temperature Range	0	25	70	°C
ІОН	Output Current – High			-0.4	mA
lOL	Output Current – Low			8.0	mA
R _{ext}	External Timing Resistance	5.0		260	kΩ
C _{ext}	External Capacitance	No Restriction			
R _{ext} /C _{ext}	Wiring Capacitance at R _{ext} /C _{ext} Terminal			50	pF



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LOW POWER SCHOTTKY



PLASTIC N SUFFIX CASE 646



SOIC D SUFFIX CASE 751A



PLASTIC N SUFFIX CASE 648



SOIC D SUFFIX CASE 751B



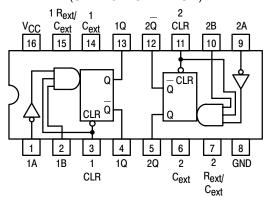
SOEIAJ M SUFFIX CASE 966

ORDERING INFORMATION

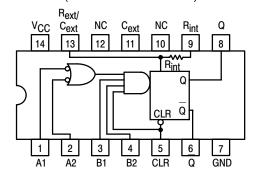
Device	Package	Shipping
SN74LS122N	14 Pin DIP	2000 Units/Box
SN74LS122D	SOIC-14	55 Units/Rail
SN74LS122DR2	SOIC-14	2500/Tape & Reel
SN74LS123N	16 Pin DIP	2000 Units/Box
SN74LS123D	SOIC-16	38 Units/Rail
SN74LS123DR2	SOIC-16	2500/Tape & Reel
SN74LS123M	SOEIAJ-16	See Note 1
SN74LS123MEL	SOEIAJ-16	See Note 1

For ordering information on the EIAJ version of the SOIC package, please contact your local ON Semiconductor representative.

SN74LS123 (TOP VIEW) (SEE NOTES 1 THRU 4)



SN74LS122 (TOP VIEW) (SEE NOTES 1 THRU 4)



NC - NO INTERNAL CONNECTION.

NOTES:

- 1. An external timing capacitor may be connected between $C_{\mbox{ext}}$ and $R_{\mbox{ext}}/C_{\mbox{ext}}$ (positive).
- 2. To use the internal timing resistor of the LS122, connect $R_{\mbox{\scriptsize int}}$ to $V_{\mbox{\scriptsize CC}}.$
- $3. \ For improved pulse width accuracy connect an external resistor between \ R_{ext}/C_{ext} \ and \ V_{CC} \ with \ R_{int} \ open-circuited.$
- 4. To obtain variable pulse widths, connect an external variable resistance between Rint/Cext and VCC.

LS122 FUNCTIONAL TABLE

	INPUTS					
CLEAR	A 1	A2	B1	B2	Q	Q
L	Х	Х	Χ	Х	L	Н
X	Н	Н	Χ	Χ	L	Н
X	Х	Χ	L	Χ	L	Н
X	Х	Χ	Χ	L	L	Н
Н	L	Χ	\uparrow	Н	л	ъ
Н	L	Χ	Н	\uparrow	小	ъ
Н	Х	L	\uparrow	Н	л	ъ
Н	Х	L	Н	\uparrow	л	ъ
Н	Н	\downarrow	Н	Н	л	ъ
Н	\downarrow	\downarrow	Н	Н	л	ъ
Н	\downarrow	Н	Н	Н	л	T
1	L	Χ	Н	Н	л	ъ
1	Χ	L	Н	Н	九	լ

LS123 FUNCTIONAL TABLE

INI	OUT	PUTS		
CLEAR	Α	В	Q	D
L	Х	Χ	L	Н
X	Н	Χ	L	Н
X	Х	L	L	Н
Н	L	\uparrow	л	ъ
Н	\downarrow	Н	Л	T
1	L	Н	几	ъ

TYPICAL APPLICATION DATA

The output pulse tw is a function of the external components, C_{ext} and R_{ext} or C_{ext} and R_{int} on the LS122. For values of $C_{ext} \ge 1000$ pF, the output pulse at $V_{CC} = 5.0$ V and $V_{RC} = 5.0$ V (see Figures 1, 2, and 3) is given by

 $t_W = K R_{ext} C_{ext}$ where K is nominally 0.45

If C_{ext} is on pF and R_{ext} is in k Ω then tw is in nanoseconds. The C_{ext} terminal of the LS122 and LS123 is an internal connection to ground, however for the best system performance C_{ext} should be hard-wired to ground.

Care should be taken to keep R_{ext} and C_{ext} as close to the monostable as possible with a minimum amount of inductance between the R_{ext}/C_{ext} junction and the R_{ext}/C_{ext} pin. Good groundplane and adequate bypassing should be designed into the system for optimum performance to ensure that no false triggering occurs.

It should be noted that the C_{ext} pin is internally connected to ground on the LS122 and LS123, but not on the LS221. Therefore, if C_{ext} is hard-wired externally to ground, substitution of a LS221 onto a LS123 socket will cause the LS221 to become non-functional.

The switching diode is not needed for electrolytic capacitance application and should not be used on the LS122 and LS123.

To find the value of K for $C_{ext} \ge 1000$ pF, refer to Figure 4. Variations on V_{CC} or V_{RC} can cause the value of K to change, as can the temperature of the LS123, LS122.

Figures 5 and 6 show the behavior of the circuit shown in Figures 1 and 2 if separate power supplies are used for V_{CC} and V_{RC}. If V_{CC} is tied to V_{RC}, Figure 7 shows how K will vary with V_{CC} and temperature. Remember, the changes in R_{ext} and C_{ext} with temperature are not calculated and included in the graph.

As long as $C_{ext} \ge 1000$ pF and $5K \le R_{ext} \le 260K$, the change in K with respect to R_{ext} is negligible.

If $C_{ext} \le 1000$ pF the graph shown on Figure 8 can be used to determine the output pulse width. Figure 9 shows how K will change for $C_{ext} \le 1000$ pF if V_{CC} and V_{RC} are connected to the same power supply. The pulse width t_W in nanoseconds is approximated by

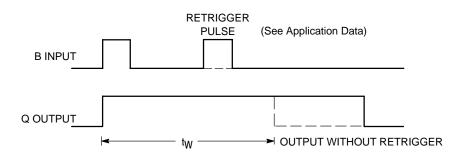
$$tW = 6 + 0.05 C_{ext} (pF) + 0.45 R_{ext} (k\Omega) C_{ext} + 11.6 R_{ext}$$

In order to trim the output pulse width, it is necessary to include a variable resistor between V_{CC} and the R_{ext}/C_{ext} pin or between V_{CC} and the R_{ext} pin of the LS122. Figure 10, 11, and 12 show how this can be done. R_{ext} remote should be kept as close to the monostable as possible.

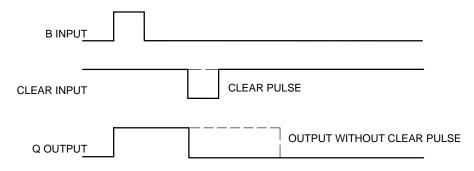
Retriggering of the part, as shown in Figure 3, must not occur before C_{ext} is discharged or the retrigger pulse will not have any effect. The discharge time of C_{ext} in nanoseconds is guaranteed to be less than 0.22 C_{ext} (pF) and is typically 0.05 C_{ext} (pF).

For the smallest possible deviation in output pulse widths from various devices, it is suggested that C_{ext} be kept ≥ 1000 pF.

WAVEFORMS



EXTENDING PULSE WIDTH



OVERRIDING THE OUTPUT PULSE

DC CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (unless otherwise specified)

			Limits					
Symbol	Parameter		Min	Тур	Max	Unit	Test C	onditions
VIH	Input HIGH Voltage		2.0			V	Guaranteed Inp All Inputs	ut HIGH Voltage for
VIL	Input LOW Voltage				0.8	V	Guaranteed Inp All Inputs	ut LOW Voltage for
VIK	Input Clamp Diode Voltage			-0.65	-1.5	V	V _{CC} = MIN, I _{IN}	= -18 mA
Vон	Output HIGH Voltage		2.7	3.5		V	V _{CC} = MIN, I _{OF} or V _{IL} per Truth	_H = MAX, V _{IN} = V _{IH} Table
				0.25	0.4	٧	I _{OL} = 4.0 mA	V _{CC} = V _{CC} MIN,
VOL	Output LOW Voltage			0.35	0.5	V	I _{OL} = 8.0 mA	V _{IN} = V _{IL} or V _{IH} per Truth Table
l	Innut I II CI I Current				20	μΑ	V _{CC} = MAX, V _I	N = 2.7 V
l IH	Input HIGH Current				0.1	mA	V _{CC} = MAX, V _I	N = 7.0 V
I _I L	Input LOW Current	Input LOW Current			-0.4	mA	V _{CC} = MAX, V _I	N = 0.4 V
los	Short Circuit Current (Note 2)	-20		-100	mA	V _{CC} = MAX	
loo	LS122				11	^		
Icc	Power Supply Current	LS123			20	mA	V _{CC} = MAX	

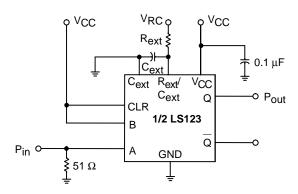
^{2.} Not more than one output should be shorted at a time, nor for more than 1 second.

AC CHARACTERISTICS ($T_A = 25$ °C, $V_{CC} = 5.0 \text{ V}$)

		Limits				
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
^t PLH	Propagation Delay, A to Q		23	33	ns	
^t PHL	Propagation Delay, A to Q		32	45	115	C _{ext} = 0
^t PLH	Propagation Delay, B to Q		23	44		$C_{\text{ext}} = 0$ $C_{\text{L}} = 15 \text{ pF}$
tPHL	Propagation Delay, B to Q		34	56	ns	$R_{\text{ext}} = 5.0 \text{ k}\Omega$
t _{PLH}	Propagation Delay, Clear to Q		28	45		$R_L = 2.0 \text{ k}\Omega$
tPHL	Propagation Delay, Clear to Q		20	27	ns	
t _W min	A or B to Q		116	200	ns	$C_{\text{ext}} = 1000 \text{ pF, } R_{\text{ext}} = 10 \text{ k}\Omega,$
t _W Q	A to B to Q	4.0	4.5	5.0	μs	$C_L = 15 \text{ pF}, R_L = 2.0 \text{ k}\Omega$

AC SETUP REQUIREMENTS (T_A = 25°C, V_{CC} = 5.0 V)

		Limits				
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
tw	Pulse Width	40			ns	



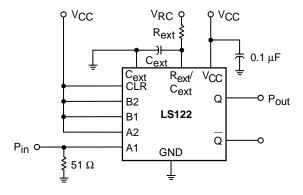


Figure 1.

Figure 2.

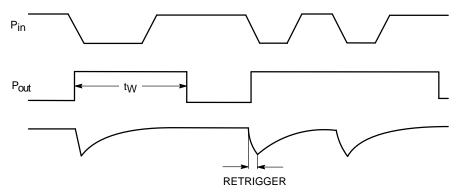


Figure 3.

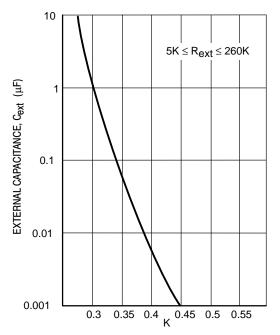
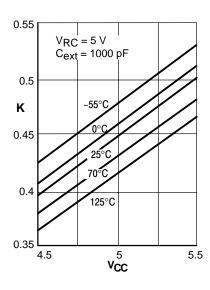
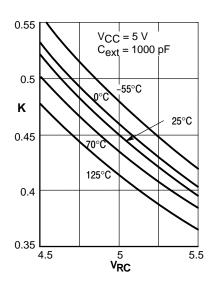


Figure 4.





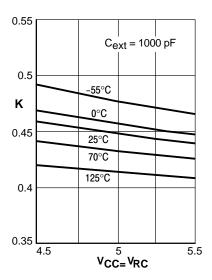


Figure 5. K versus V_{CC}

Figure 6. K versus V_{RC}

Figure 7. K versus V_{CC} and V_{RC}

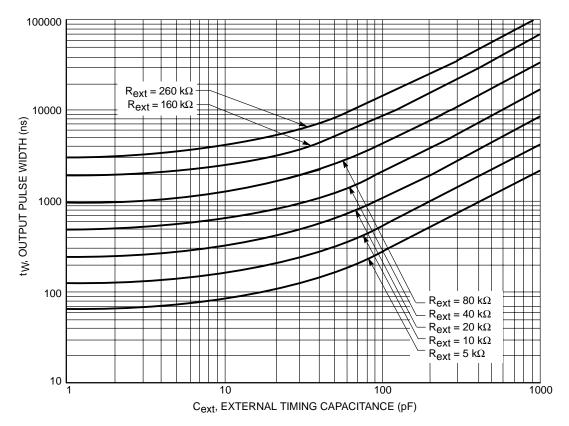


Figure 8.

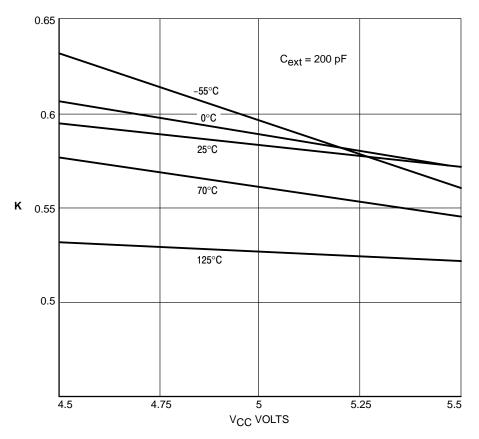


Figure 9.

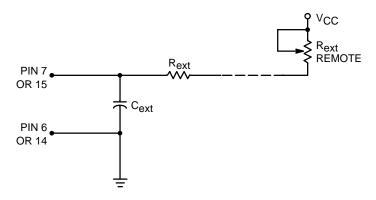


Figure 10. LS123 Remote Trimming Circuit

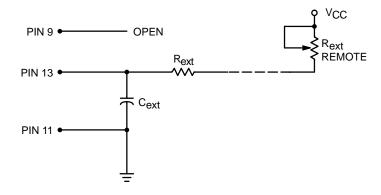


Figure 11. LS122 Remote Trimming Circuit Without Rext

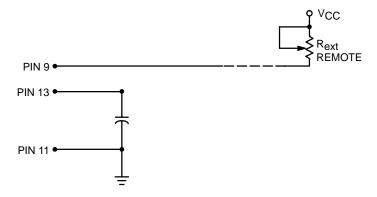
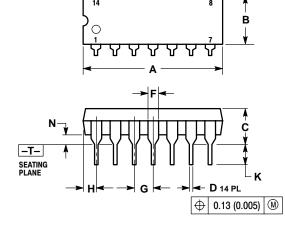
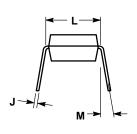


Figure 12. LS122 Remote Trimming Circuit with Rint

PACKAGE DIMENSIONS

N SUFFIX PLASTIC PACKAGE CASE 646-06 ISSUE M



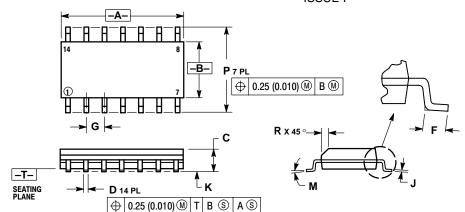


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.715	0.770	18.16	18.80	
В	0.240	0.260	6.10	6.60	
С	0.145	0.185	3.69	4.69	
D	0.015	0.021	0.38	0.53	
F	0.040	0.070	1.02	1.78	
G	0.100	BSC	2.54 BSC		
Н	0.052	0.095	1.32	2.41	
J	0.008	0.015	0.20	0.38	
K	0.115	0.135	2.92	3.43	
L	0.290	0.310	7.37	7.87	
M		10°		10°	
N	0.015	0.030	0.30	1.01	

D SUFFIX

PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE F



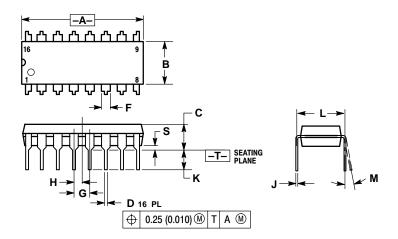
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0 °	7°	
P	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS

N SUFFIX PLASTIC PACKAGE CASE 648-08 ISSUE R

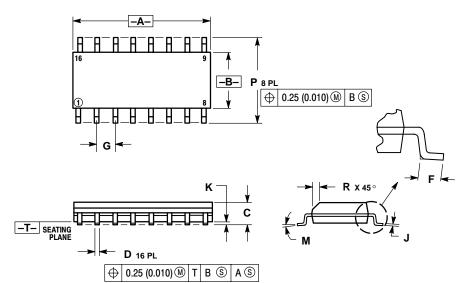


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIONING AND TOLERANGING FER AN.

 Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54 BSC		
Н	0.050	BSC	1.27 BSC		
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
М	0°	10 °	0°	10 °	
S	0.020	0.040	0.51	1.01	

D SUFFIX PLASTIC SOIC PACKAGE CASE 751B-05 **ISSUE J**



NOTES:

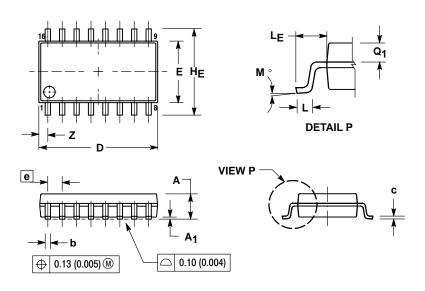
- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
 PER SIDE.
- PEH SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS

M SUFFIX

SOEIAJ PACKAGE CASE 966-01 **ISSUE O**



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018)

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
Α ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10 °
Q ₁	0.70	0.90	0.028	0.035
Z		0.78		0.031

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